



S/N 09/944981

**PATENT****IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Kie Y. Ahn et al. Examiner: Walter Lindsay  
Serial No.: 09/944981 Group Art Unit: 2812  
Filed: August 30, 2001 Docket: 1303.021US1  
Title: CRYSTALLINE OR AMOPHOUS MEDIUM-K GATE OXIDES, Y203 AND  
GD203

**COMMUNICATION CONCERNING RELATED APPLICATION(S)**

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Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2
10/028643	December 20, 2001	1303.030US1	LOW-TEMPERATURE GROWN HIGH QUALITY ULTRA-THIN CoTiO3 GATE DIELECTRICS
10/052983	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrOxNy
10/027315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/099194	March 13, 2002	1303.044US1	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELECTRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAlO3 FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO3 FILMS FOR GATE DIELECTRICS

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COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

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10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO <sub>3</sub> FILMS FOR GATE DIELECTRICS
10/163686	June 5, 2002	1303.059US1	Pr <sub>2</sub> O <sub>3</sub> -BASED La-oxide GATE DIELECTRICS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiO <sub>x</sub> DIELECTRIC FILMS BY PLASMA OXIDATION
10/219878	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiO <sub>x</sub> DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiO <sub>x</sub> DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN- TI-O FILMS USING TiH <sub>4</sub>
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn- Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAl <sub>x</sub> O <sub>y</sub> DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO <sub>4</sub> FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS

COMMUNICATION CONCERNING CO-PENDING APPLICATIONS

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Respectfully submitted,

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